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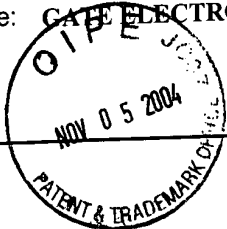
TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
FIS920040196US1

In Re Application: Gluschenkov et al.

Application No. 10/711,642	Filing Date 9/29/04	Examiner not assigned	Customer No. 45094	Group Art Unit not assigned	Confirmation No. not assigned
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Title: **CABLE ELECTRODE FORMING METHODS USING CONDUCTIVE HARD MASK**



Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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Lisa U. Jaklitsch
Signature

Dated: 11/3/04

Lisa U. Jaklitsch
Reg. No. 45,168

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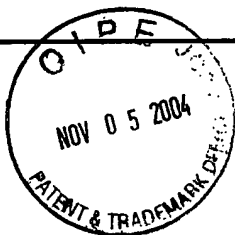
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In Re Application Of: **Gluschenkov et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/711,642	9/29/04	not assigned	45094	not assigned	not assigned

Title: **GATE ELECTRODE FORMING METHODS USING CONDUCTIVE HARD MASK**



Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

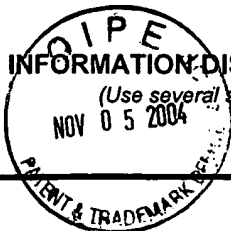
37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

OR

☐ the fee set forth in 37 CFR 1.17(p).



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

NOV 05 2004

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Gluschenkov, et al.

FILING

9/29/04

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,888,588	3/30/99	NAGABUSHNAM, ET AL.			
	6,340,629	1/22/02	YEO, ET AL.			
	6,162,715	12/19/00	MAK, ET AL.			
	6,274,484	08/14/01	TSAI, ET AL.			
	6,096,641	8/01/00	KUNIKIYO			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		"A Model of Bonding and Band-forming For Oxides And Nitrides", by Chang Sun, 1998 The American Institute of Physics, Applied Physics Letters, Vol. 72, No. 14, April 6, 1998, Pgs. 1706-1708
		"Theory Of Bonding In Transition-metal Carbides And Nitrides", by J. Haglund, 1993 The American Physical Society, Physical Review B, Vol. 48, No. 16, 10/15/1993 pgs. 685-691

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		CHAU, R., et al., "Gate Dielectric Scaling for High-Performance CMOS: from SiO2 to High-K," International Workshop on Gate Insulator 2003, Tokyo, Japan, November 2003, pp. 124 - 126.
		"Intel's High-k/Metal Gate Announcement," www.cse.psu.edu/~cg477/sp04/misc/highK.pdf, November 2003, pp. 1-17.

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							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			PARK, D.-G., et al., "Thermally Robust Dual-Work Function ALD-MNx MOSFETs Using Conventional CMOS Process Flow," 2004 Symposium on VLSI Technology, Digest of Technical Papers, pp. 186-187.

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